

L Number	Hits	Search Text	DB	Time stamp
1	6	((("5753554") or ("6368920") or ("6307231"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 13:42
2	7598	257/244,283,284,301-305,330-334,618-628.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 13:47
3	41	257/244,283,284,301-305,330-334,618-628.ccls. and (MISFET with (groove trench))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 14:19
4	3	("4689871" "4954854" "5122848").PN.	USPAT	2004/06/23 14:00
5	8	("5366914" "5479037" "5558313" "5578508" "5907776" "5918114" "5940721" "5981344").PN.	USPAT	2004/06/23 14:01
6	6	("4742015" "5135880" "5248627" "5527720" "5567634" "5648288").PN.	USPAT	2004/06/23 14:03
7	10	("4573066" "4707719" "4774560" "4914058" "4931846" "4983535" "5072266" "5160491" "5387528" "5405794").PN.	USPAT	2004/06/23 14:04
8	11	("4573066" "4707719" "4774560" "4830981" "4904613" "4914058" "4920064" "4983535" "5072266" "5160491" "5242845").PN.	USPAT	2004/06/23 14:06
9	9	("4653177" "4893160" "4994409" "5029324" "5034785" "5047359" "5126807" "5168331" "5364810").PN.	USPAT	2004/06/23 14:08
10	3	("5023196" "5128278" "5182222").PN.	USPAT	2004/06/23 14:10
11	6	("4333794" "4381953" "4385975" "4569701" "4582565" "4593459").PN.	USPAT	2004/06/23 14:13
12	2	("5918114").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 14:18
13	2	("4685196" "5362665").PN.	USPAT	2004/06/23 14:16
14	6	("4689871" "4829017" "4891327" "5192704" "5244824" "5270239").PN.	USPAT	2004/06/23 14:17
15	346097	257/\$.ccls. 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 14:19
16	245	(257/\$.ccls. 438/\$.ccls.) and (MISFET with (groove trench))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 14:20
17	15	("3975221" "4003126" "4084175" "4272302" "5258332" "5693569" "5733810" "5744826" "5753554" "5783491" "5817558" "6307231" "6368920" "6455378" "6511886").PN.	USPAT	2004/06/23 14:33
18	3	("4992390" "5473176" "6198127").PN.	USPAT	2004/06/23 14:34
19	15	("4546367" "4589193" "4767722" "4921815" "4941026" "4992838" "5016068" "5040034" "5196373" "5248894" "5321289" "5385853" "5410170" "5468982" "5726088").PN.	USPAT	2004/06/23 14:34
20	10	("4830975" "4939100" "4959326" "5155053" "5405787" "5552329" "5580803" "5688704" "5698461" "5736435").PN.	USPAT	2004/06/23 14:37
21	13	("4666556" "4835585" "5237187" "5612557" "5621232" "5717254" "5734175" "5972768" "6008114" "6107196" "6406998" "6472317" "6482735").PN.	USPAT	2004/06/23 14:40
22	1	"4353086".PN.	USPAT	2004/06/23 14:49

L Number	Hits	Search Text	DB	Time stamp
1	303	(257/\$.ccls. 438/\$.ccls.) and (MISFET with MOSFET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:17
2	3	((257/\$.ccls. 438/\$.ccls.) and (MISFET with MOSFET)) and ((gate near (wir\$3 electrode contact)) near2 (trench groove) near2 ((insulat\$3 dielectric) near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:21
3	256	((gate near (wir\$3 electrode contact)) near2 (trench groove) near2 ((insulat\$3 dielectric) near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:22
4	0	((gate near (wir\$3 electrode contact)) near2 outside near2 (trench groove) near2 ((insulat\$3 dielectric) near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:31
5	13	((gate near (wir\$3 electrode contact)) near2 (trench groove) near2 ((insulat\$3 dielectric) near (layer film))) and MISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:07
6	0	((gate near (wir\$3 electrode contact)) near2 (form\$3 near on) near2 ((insulat\$3 dielectric) near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:05
7	0	gate near2 (form\$3 near on) near2 ((insulat\$3 dielectric) near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:30
8	0	((gate near (wir\$3 electrode contact)) with (form\$3 near on) with ((insulat\$3 dielectric) near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:30
9	0	((gate near (wir\$3 electrode contact)) same (form\$3 near on) same ((insulat\$3 dielectric) near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:30
10	22	(gate near (wir\$3 electrode contact)) near2 outside near2 (trench groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:03
11	25	((gate metal) near (wir\$3 electrode contact)) near2 outside near2 (trench groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:04
12	0	(wir\$3 electrode contact) near2 (form\$3 near on) near2 ((insulat\$3 dielectric) near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:07

13	0	(form\$3 near on) near2 ((insulat\$3 dielectric) near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:06
14	0	(form\$3 near on) near ((insulat\$3 dielectric) near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:06
15	42552	(wir\$3 electrode contact) near2 form\$3 near2 ((insulat\$3 dielectric) near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:07
16	908	((wir\$3 electrode contact) near2 form\$3 near2 ((insulat\$3 dielectric) near (layer film))) and MISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:09
17	15543	(gate conduct\$3 metal) near (wir\$3 electrode contact) near2 form\$3 near2 ((insulat\$3 dielectric) near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:10
18	721	((gate conduct\$3 metal) near (wir\$3 electrode contact) near2 form\$3 near2 ((insulat\$3 dielectric) near (layer film))) and MISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:10
19	27941	(gate conduct\$3 metal) near (wir\$3 electrode contact) near2 ((insulat\$3 dielectric) near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:10
20	1303	((gate conduct\$3 metal) near (wir\$3 electrode contact) near2 ((insulat\$3 dielectric) near (layer film))) and MISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:10
21	846	((gate conduct\$3 metal) near (wir\$3 electrode contact) near2 ((insulat\$3 dielectric) near (layer film))) and MISFET and (source with drain with (base channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:11
22	513	((gate conduct\$3 metal) near (wir\$3 electrode contact) near2 ((insulat\$3 dielectric) near (layer film))) and MISFET and (source near3 drain near3 (base channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:12
23	300	((gate conduct\$3 metal) near (wir\$3 electrode contact) near2 ((insulat\$3 dielectric) near (layer film))) and MISFET and (source near2 drain near2 (base channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:12
24	176	((gate conduct\$3 metal) near (wir\$3 electrode contact) near2 ((insulat\$3 dielectric) near (layer film))) and MISFET and ((source near (layer region)) near2 (drain near (layer region)) near2 (base channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:13